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**GI850/MR850 thru GI858/MR858**  
**3 Amp Fast Switching Plastic Rectifier**  
**DO-201AD Type Package**

**Features:**

- High Forward Surge Capability
- Fast Switching for High Efficiency
- High Forward Current Operation

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Maximum Repetitive Peak Reverse and Blocking Voltage,  $V_{RRM}, V_{DC}$

GI850/MR850	.....	50V
GI851/MR851	.....	100V
GI852/MR852	.....	200V
GI854/MR854	.....	400V
GI856/MR856	.....	600V
GI858/MR858	.....	800V

Maximum RMS Voltage,  $V_{RMS}$

GI850/MR850	.....	35V
GI851/MR851	.....	70V
GI852/MR852	.....	140V
GI854/MR854	.....	280V
GI856/MR856	.....	420V
GI858/MR858	.....	510V

Maximum Non-Repetitive Peak Reverse Voltage,  $V_{RSM}$

GI850/MR850	.....	75V
GI851/MR851	.....	150V
GI852/MR852	.....	250V
GI854/MR854	.....	450V
GI856/MR856	.....	650V
GI858/MR858	.....	880V

Maximum Average Forward Rectified Current,  $I_{F(AV)}$

$T_A = +90^\circ\text{C}$ , .375" (9.5mm) Lead Length ..... 3A

Peak Forward Surge Current,  $I_{FSM}$

8.3ms single half sine-wave superimposed on rated load ..... 100A

Operating Junction Temperature Range,  $T_J$  .....  $-50^\circ$  to  $+150^\circ\text{C}$

Storage Temperature Range,  $T_{STG}$  .....  $-50^\circ$  to  $+150^\circ\text{C}$

Typical Thermal Resistance (Note 1)

Junction-to-Ambient,  $R_{thJA}$  .....  $22^\circ\text{C/W}$

Junction-to-Lead,  $R_{thJL}$  .....  $8.0^\circ\text{C/W}$

Note 1. Thermal resistance from junction to ambient and from junction to lead at 0.375" (9.5mm) lead length

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	$V_F$	$I_F = 3\text{A}$	-	-	1.25	V
		$I_F = 9.4\text{A}, T_J = +175^\circ\text{C}$	-	-	1.1	V
DC Reverse Current All Devices	$I_R$	$T_A = +25^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$T_A = +100^\circ\text{C}$	$V_{DC} = 50\text{V}$	-	-	150 $\mu\text{A}$
			$V_{DC} = 100\text{V}$	-	-	150 $\mu\text{A}$
			$V_{DC} = 200\text{V}$	-	-	200 $\mu\text{A}$
			$V_{DC} = 400\text{V}$	-	-	250 $\mu\text{A}$
			$V_{DC} = 600\text{V}$	-	-	300 $\mu\text{A}$
			$V_{DC} = 800\text{V}$	-	-	500 $\mu\text{A}$
Junction Capacitance	$C_J$	$V_R = 4\text{V}, f = 1\text{MHz}$	-	28	-	pF
Reverse Recovery Time	$t_{rr}$	$I_F = 1\text{A}, V_R = 30\text{V}, di/dt = 50\text{A}/\mu\text{s},$ $t_{rr} = 10\% I_{RM}$	-		200	ns
Reverse Recovery Current	$I_{RM(REC)}$	$I_F = 1\text{A}, V_R = 30\text{V}, di/dt = 50\text{A}/\mu\text{s},$ $t_{rr} = 10\% I_{RM}$	-		2	A

